



SSCL090P60GN6

P-Channel Enhancement Mode MOSFET

➤ Features

V _{DS}	V _{GS}	R _{DS(ON)} Typ.	I _D
-60V	±20V	7.5mΩ@-10V	-87A
		10mΩ@-4.5V	

➤ Description

This device is P-Channel enhancement MOSFET. Uses SGT technology and design to provide excellent R_{DS(ON)} with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit.

100% UIS + ΔVDS + R_g Tested!

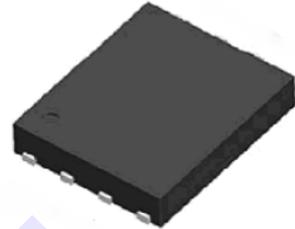
➤ Applications

- Load Switch
- PWM Application
- Power Management
- DC/DC Conversion

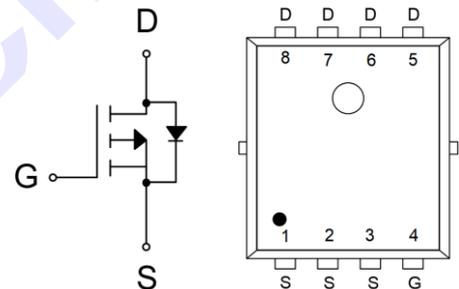
➤ Ordering Information

Device	Package	Shipping
SSCL090P60GN6	PDFN5X6-8L	5000/Reel

➤ Pin configuration



PDFN5X6-8L (Top View)



Pin Configuration



Marking

(XYYY: Internal Traceability Code)



➤ **Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Unit	
V_{DSS}	Drain-to-Source Voltage	-60	V	
V_{GSS}	Gate-to-Source Voltage	± 20	V	
I_D	Continuous Drain Current ^d	$T_C=25^\circ\text{C}$	-87	A
		$T_C=100^\circ\text{C}$	-55	
I_{DSM}	Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	-13	A
		$T_A=70^\circ\text{C}$	-11	
I_{DM}	Pulsed Drain Current ^b	-348	A	
P_D	Power Dissipation ^c	$T_C=25^\circ\text{C}$	125	W
		$T_C=100^\circ\text{C}$	50	
P_{DSM}	Power Dissipation ^a	$T_A=25^\circ\text{C}$	2.8	W
		$T_A=70^\circ\text{C}$	1.8	
I_{AS}	Avalanche Current ^b L=0.5mH Single Pulse	-40	A	
E_{AS}	Avalanche Energy ^b L=0.5mH Single Pulse	410	mJ	
T_J	Operation junction temperature	-55~150	$^\circ\text{C}$	
T_{STG}	Storage temperature range	-55~150		

➤ **Thermal Resistance Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)**

Symbol	Parameter	Ratings	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance ^a	44	55	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance	1.0	1.3	

Note:

- The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz.copper, in a still air environment with $T_A=25^\circ\text{C}$. The value in any given application depends on the user is specific board design. The power dissipation is based on the $t \leq 10\text{s}$ thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation P_D is based on $T_{J(MAX)}=150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.
- The maximum current rating is package limited.

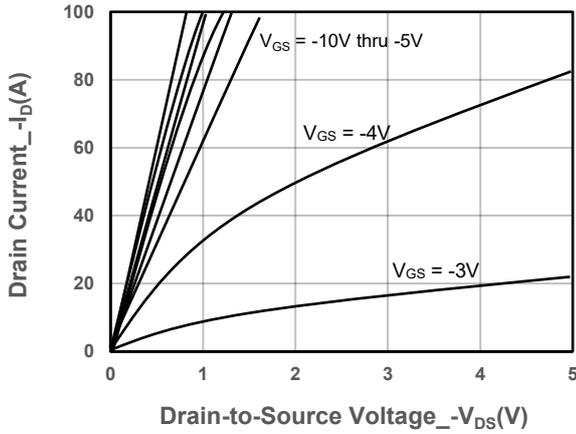


➤ **Electrical Characteristics (T_A=25°C unless otherwise noted)**

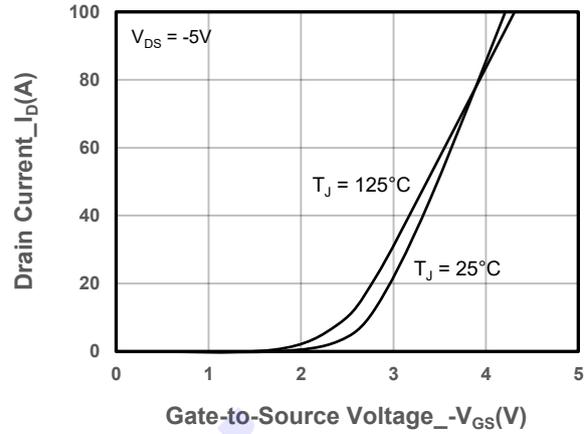
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250uA	-1	-1.8	-2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -20A		7.5	10	mΩ
		V _{GS} = -4.5V, I _D = -10A		10	13	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0V			-1	μA
Gate-Source Leak Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Transconductance	G _{FS}	V _{DS} = 5V, I _D = -10A		43		S
Forward Voltage	V _{SD}	V _{GS} = 0V, I _S = -10A		-0.8	-1.3	V
Gate Resistance	R _G	V _{DS} = 0V, f = 1MHz		4.8		Ω
Input Capacitance	C _{ISS}	V _{DS} = -30V, V _{GS} = 0V, f = 1MHz		3610		pF
Output Capacitance	C _{OSS}			902		
Reverse Transfer Capacitance	C _{RSS}			40		
Total Gate Charge	Q _G	V _{GS} = -10V, V _{DS} = -30V, I _D = -20A		49		nC
Gate to Source Charge	Q _{GS}			11		
Gate to Drain Charge	Q _{GD}			6		
Turn-on Delay Time	T _{D(ON)}	V _{GS} = -10V, V _{DS} = -30V, I _D = -20A, R _G = 3Ω,		6		ns
Rise Time	T _r			13		
Turn-off Delay Time	T _{D(OFF)}			65		
Fall Time	T _f			22		
Diode Recovery Time	T _{rr}	I _F =-20A, di/dt=100A/us		45		ns
Diode Recovery Charge	Q _{rr}	I _F =-20A, di/dt=100A/us		53		nC



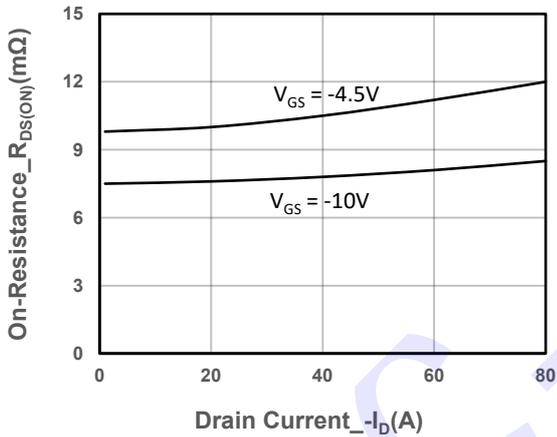
Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)



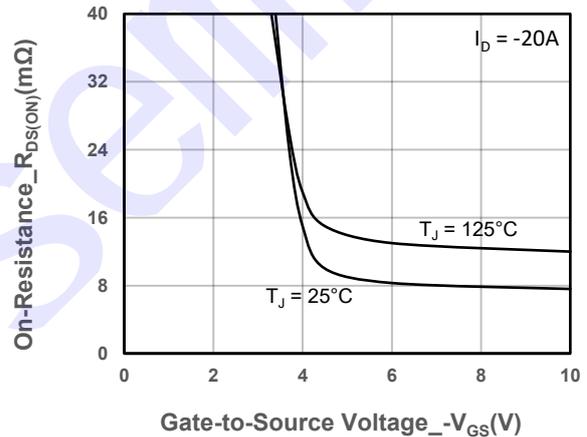
Output Characteristics



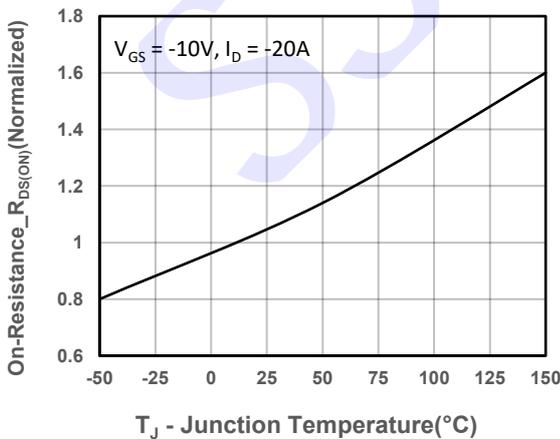
Transfer Characteristics



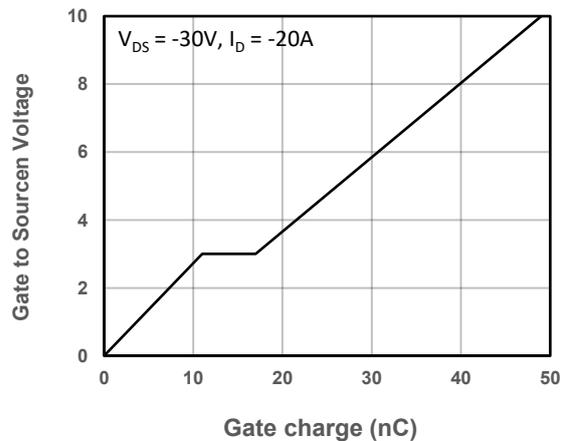
On-Resistance vs. Drain Current and Gate Voltage



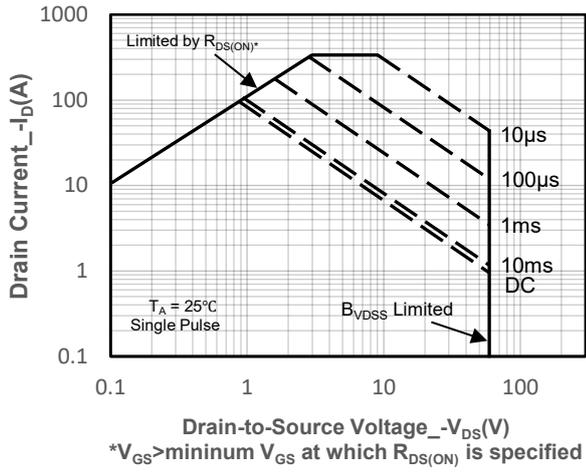
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



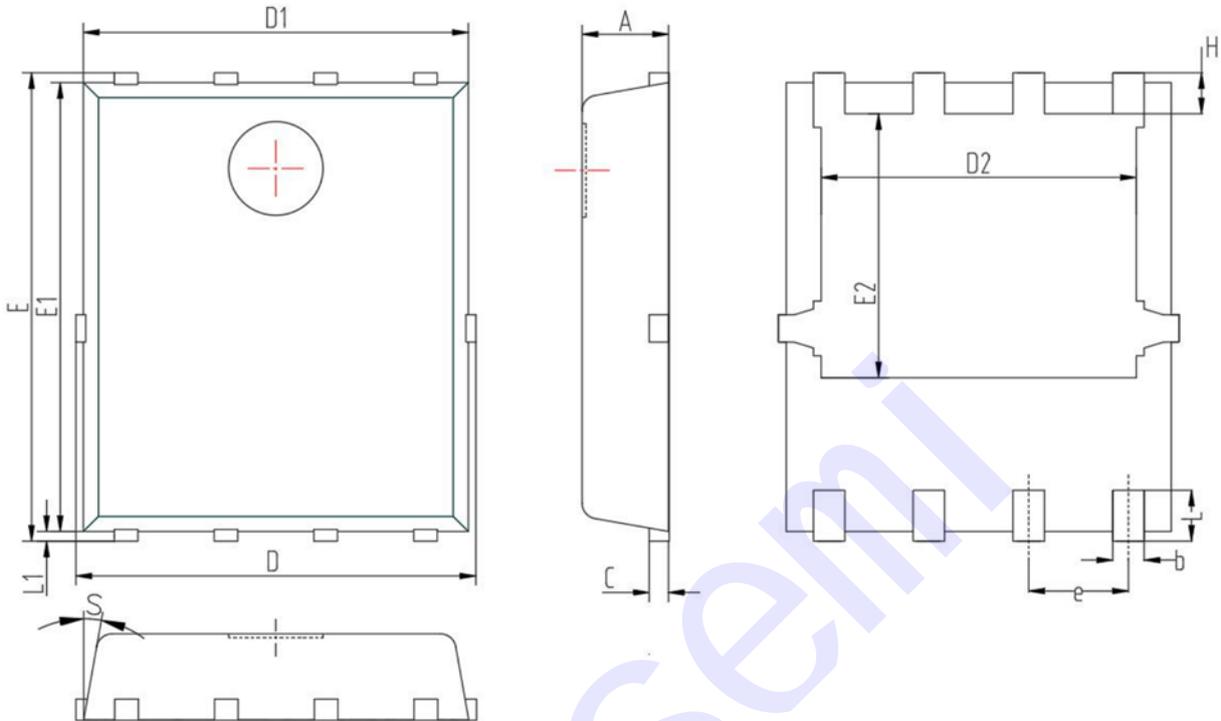
Gate-Source Voltage vs. Gate charge



Safe Operating Area vs. Junction-to-Ambient

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➤ Package Information



Symbol	MILL IMETER		
	Min	Nom	Max
A	0.90	1.05	1.20
b	0.25	0.30	0.51
c	0.15	0.25	0.35
D	4.80	5.10	5.40
D1	4.80	5.00	5.20
D2	3.70	4.00	4.30
E	5.80	6.15	6.50
E1	5.50	5.75	5.95
E2	3.30	3.45	3.67
e	1.27BSC		
H	0.40	0.60	0.93
L	0.45	0.65	0.85
L1	0.00	0.10	0.25
S	0°	--	12°



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